



Application No. 09/295,607  
Docket No. 740756-1961

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

International Patent Application of:

Shunpei YAMAZAKI et al.

Serial No. 09/295,607

Filed: April 22, 1999

For: SEMICONDUCTOR DEVICE HAVING

ALUMINUM NITRIDE FILM

Examiner: Steven Ho Yin Loke

Group Art Unit: 2811

Confirmation No. 7371

CERTIFICATE OF MAILING OR TRANSMISSION

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage for First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on December 31, 2003.

Signature:

Name:

*D. Movahhedi*  
*D. Movahhedi*

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

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Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. §1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98. Pursuant to 37 C.F.R. § 1.98, a copy of each of the documents cited is enclosed.

The documents are being submitted before the first Office Action on the merits, therefore no fee or certification is required under 37 C.F.R. § 1.97(b).

Applicants note that U.S. Patent No. 5,192,644 and U.S. Patent No. 4,832,986 are cited for disclosing an AlN film. Further, the JP 03-175632 and HSIEH, J.J., et al., "DIRECTIONAL DEPOSITION OF DIELECTRIC SILICON OXIDE BY PLASMA ENHANCED TEOS PROCESS" references were cited in a family application Serial No. 09/432,106, and the JP 58-085520, JP 62-214669, JP 02-033935, and JP 04-139727 references were cited in a counterpart Japanese patent application which were made available to Applicants on October 28, 2003.

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It is requested that the accompanying PTO-1449 be considered and made of record in the above-identified application. To assist the Examiner, the documents are listed on the attached form PTO-1449. It is respectfully requested that an Examiner initialed copy of this form be returned to the undersigned.

The Commissioner is hereby authorized to charge any fees connected with this filing which may be required now, or credit any overpayment to Deposit Account No. 19-2380. (740756-1961)

Respectfully submitted,  
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By: 

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Substitute for Form <b>PRO-APP-1</b>		<b>Complete if Known</b>			
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)		Application Number	09/295,607		
		Filing Date	April 22, 1999		
		First Named Inventor	Shunpei YAMAZAKI		
		Art Unit	2811		
		Examiner Name	Steven Ho Yin Loke		
Sheet	1	of	1	Attorney Docket Number	740756-1961

U.S. PATENT DOCUMENTS					
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
		US-4,832,986	05-23-1989	Gladfelter et al.	
		US-5,192,644	03-09-1993	Ohta et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Kind Code <sup>2</sup> (if known)				
		JP 58-085520	05-21-1983	Koba		Abstract
		JP 62-214669	09-21-1987	Kaneko et al.		Abstract
		JP 02-033935	02-05-1990	Yazaki		Abstract
		JP 03-175632	07-30-1991	Fujiki et al.		Abstract
		JP 04-139727	05-13-1992	Matsumoto et al.		Abstract

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>3</sup>
		HSIEH, J.J., ET AL., "DIRECTIONAL DEPOSITION OF DIELECTRIC SILICON OXIDE BY PLASMA ENHANCED TEOS PROCESS", VMIC CONFERENCE, PP. 411-415, 1989	

Examiner Signature	/Shouxiang Hu/	Date Considered	03/11/2009
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

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